

# NOT RECOMMENDED FOR NEW DESIGN USE DMTH10H025LK3



DMTH10H030LK3

#### 100V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET

### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> T <sub>C</sub> = +25°C
1001/	30mΩ @ V <sub>GS</sub> = 10V	28A
100V	45mΩ @ V <sub>GS</sub> = 6.0V	23A

### Description

This new generation MOSFET features low on-resistance and fast switching, making it ideal for high efficiency power management applications.

### **Applications**

- Power Management Functions
- DC-DC Converters
- Backlighting

### **Features**

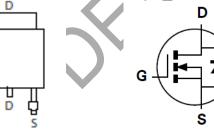
- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching Ensures More Reliable and Robust End Application
- Low R<sub>DS(ON)</sub> Minimizes Power Losses
- Low Q<sub>G</sub> Minimizes Switching Losses
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

### **Mechanical Data**

- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.33 grams (Approximate)



Top View



**Equivalent Circuit** 

### Ordering Information (Note 4)

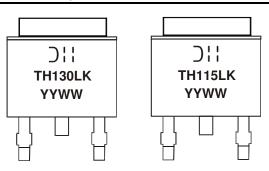
Part Number	Case	Packaging
DMTH10H030LK3-13	TO252 (DPAK)	2,500/Tape & Reel

Pin Out Top View

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

## **Marking Information**



Oll = Manufacturer's Marking
TH130LK or TH115LK = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 17 = 2017)
WW = Week Code (01 to 53)



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# **Maximum Ratings** (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage		$V_{DSS}$	100	V
Gate-Source Voltage		$V_{GSS}$	±20	V
Continuous Drain Current, V <sub>GS</sub> = 10V	I <sub>D</sub>	28 18	А	
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)		I <sub>DM</sub>	150	Α
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)		I <sub>SM</sub>	150	Α
Maximum Continuous Body Diode Forward Current (Note 6)		Is	2.6	Α
Avalanche Current, L = 3mH		I <sub>AS</sub>	7.5	Α
Avalanche Energy, L = 3mH		E <sub>AS</sub>	85	mJ

## Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

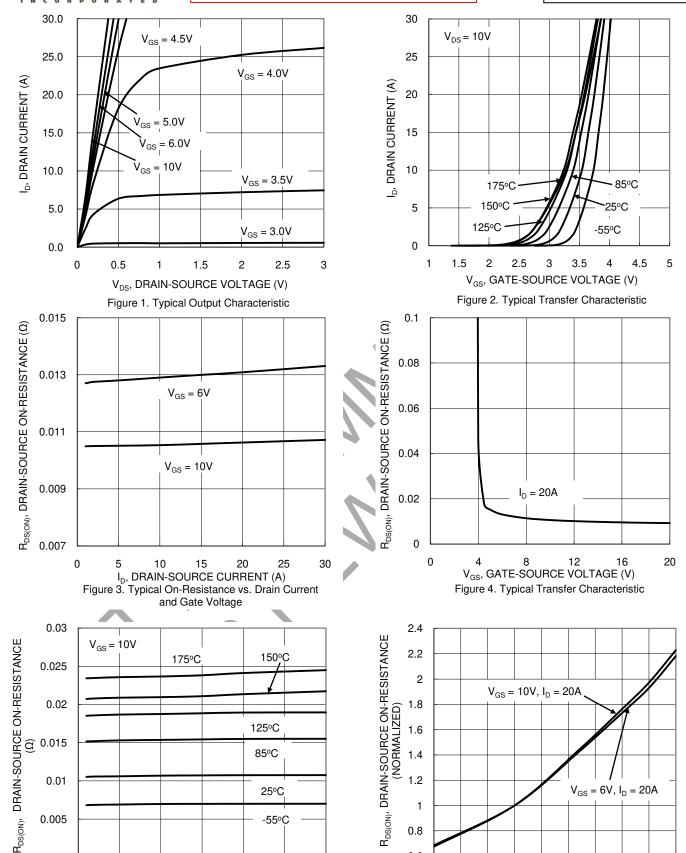
Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		P <sub>D</sub>	2.1	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R <sub>0JA</sub>	69	°C/W
Total Power Dissipation (Note 6)		Pb	3.5	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R <sub>0</sub> JA	42	°C/W
Thermal Resistance, Junction to Case	A 11	R <sub>0</sub> JC	2	C/VV
Operating and Storage Temperature Range		$T_{J,}T_{STG}$	-55 to +175	°C

# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	$BV_{DSS}$	100		_	٧	$V_{GS} = 0V$ , $I_D = 1mA$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	1		1	μΑ	$V_{DS} = 80V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>		_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1.4	_	3.5	٧	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance		<b>V</b> _	_	30	mΩ	$V_{GS} = 10V, I_D = 20A$	
Static Diani-Source On-nesistance	RDS(ON)	_	_	45	11122	$V_{GS} = 6.0V, I_D = 20A$	
Diode Forward Voltage	$V_{SD}$	1	_	1.3	V	$V_{GS} = 0V, I_S = 20A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C <sub>iss</sub>	_	1,871	_		$V_{DS} = 50V$ , $V_{GS} = 0V$ f = 1MHz	
Output Capacitance	Coss		261		pF		
Reverse Transfer Capacitance	C <sub>rss</sub>	-	6.9				
Gate Resistance	$R_{G}$	1	0.75	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge	Q <sub>G</sub>	-	33.3			V 50V L 40A	
Gate-Source Charge	Q <sub>GS</sub>	1	6.9	_	nC	$V_{DD} = 50V, I_D = 10A,$ $V_{GS} = 10V$	
Gate-Drain Charge	$Q_{GD}$	-	5.1				
Turn-On Delay Time	t <sub>D(ON)</sub>		6.5	_		$V_{DD} = 50V, V_{GS} = 10V,$ $I_{D} = 10A, R_{G} = 6\Omega$	
Turn-On Rise Time	t <sub>R</sub>	1	7.0	_	ns		
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	19.7	_	115		
Turn-Off Fall Time	t <sub>F</sub>		8.1				
Reverse Recovery Time	t <sub>RR</sub>	_	37.9	_	ns	L 104 di/dt 1004/va	
Reverse Recovery Charge	Q <sub>RR</sub>	_	51.9	_	nC	I <sub>F</sub> = 10A, di/dt = 100A/μs	

Notes:

- 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate.
- 7. Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to product testing.



I<sub>D</sub>, DRAIN CURRENT (A) Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

20

15

10

25°C

-55°C

25

5

0.01

0.005

0

0

30

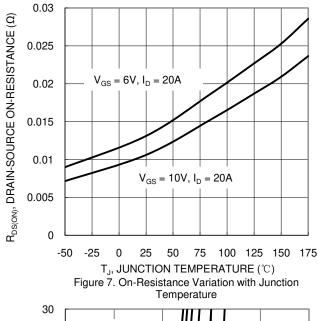
1.2

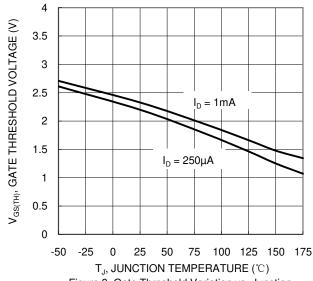
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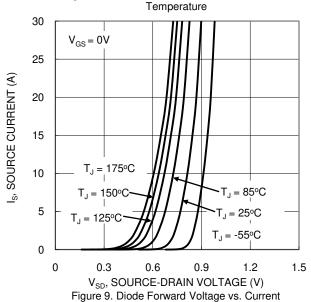
0.8

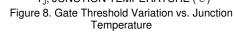
0.6

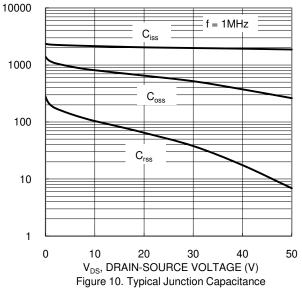
 $V_{GS} = 6V, I_{D} = 20A$ 

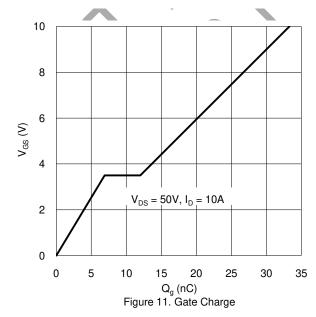


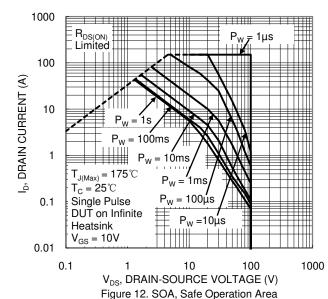












C<sub>T</sub>, JUNCTION CAPACITANCE (pF)



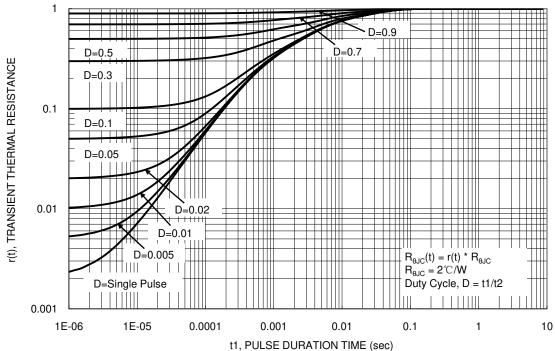
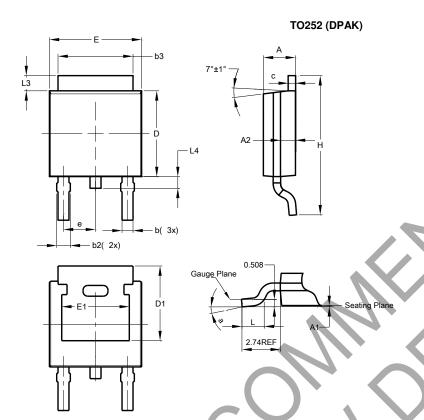


Figure 13. Transient Thermal Resistance



# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

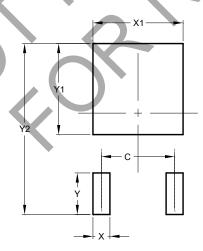


TO252 (DPAK)					
Dim	Min	Max	Тур		
Α	2.19	2.39	2.29		
<b>A</b> 1	0.00	0.13	0.08		
A2	0.97	1.17	1.07		
q	0.64	0.88	0.783		
b2	0.76	1.14	0.95		
b3	5.21	5.46	5.33		
O	0.45	0.58	0.531		
J	6.00	6.20	6.10		
D1	5.21	-/			
е	-		2.286		
П	6.45	6.70	6.58		
E1 .	4.32	-	-		
H	9.40	10.41	9.91		
Þ	1.40	1.78	1.59		
L3	0.88	1.27	1.08		
L4	0.64	1.02	0.83		
а	0°	10°	-		
All Dimensions in mm					

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.





Dimensions	Value (in mm)		
С	4.572		
Х	1.060		
X1	5.632		
Υ	2.600		
Y1	5.700		
Y2	10.700		



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